IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 09/834,660
Priority Filing Date ..... April 12, 2001
Inventor .....Luan C. Tran
Assignee..... Micron Technology, Inc.
Priority Group Art Unit 2813
Priority Examiner .....L. Schillinger
Attorney's Docket No. MI22-1921
Title: Semiconductor Processing Methods Of Forming Transistors, Semiconductor Processing Methods Of Forming Dynamic Random Access Memory Circuitry, And Related Integrated Circuitry

37 CFR § 1.121(b)(1)(iii) AND 37 CFR § 1.121(c)(1)(ii) FILING REQUIREMENTS TO ACCOMPANY PRELIMINARY AMENDMENT

Deletions are bracketed, additions are underlined.

In the Specification

On page 1, after the title, insert:

CROSS REFERENCE TO RELATED APPLICATION

This patent application is a Divisional Application of U.S. Patent Application Serial No. 09/834,660, filed April 12, 2001, entitled "Semiconductor Processing Methods Of Forming Transistors, Semiconductor Processing Methods Of Forming Dynamic Random Access Memory Circuitry, And Related Integrated Circuitry," naming Luan C. Tran as inventor, which is a Divisional Application of U.S. Patent Application Serial No. 09/388,857, filed September 1, 1999, the disclosure of which is incorporated by reference.

The paragraph beginning on page 10, line 21, and extending through p. 11, line 9, has been amended as follows:

Also shown in Fig. 7 is a sense amplifier circuit 50 including cross-coupled transistors 52 and 54. In one embodiment, the transistors 52 and 54 are formed to have a low threshold voltage V_{tl}. When the signal CSAL goes to logic "1", the common node labeled RNL* equilibrates the potentials on sources of the transistors 52 and 54 in preparation for reading stored data from memory cells in a memory array (not shown). In the example shown in Fig. 7, the circuit 40 acts as a pull-down circuit and equilibrates the node RNL* to ground. Use of multiple transistors 42, 44 and 46 having different threshold voltages facilitates ("softens") sensing at the beginning of the sensing cycle and also facilitates more rapid sensing at the end of the cycle when differential signals have been developed by the transistors 52 and 54.

In the Drawings

Figs. 3-7 have been modified as shown in the enclosed marked-up-in-red copies thereof. Substitute formal drawings are also enclosed, including corrected Figs. 3-7.